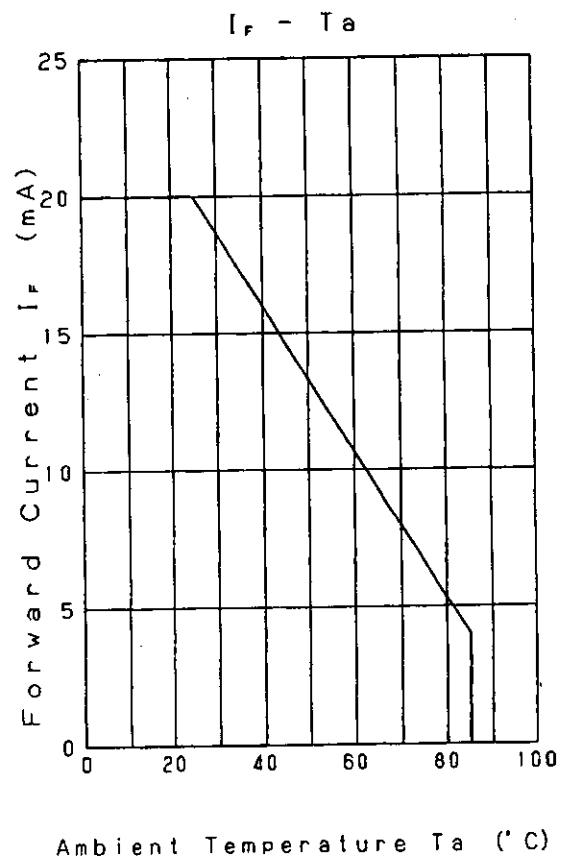
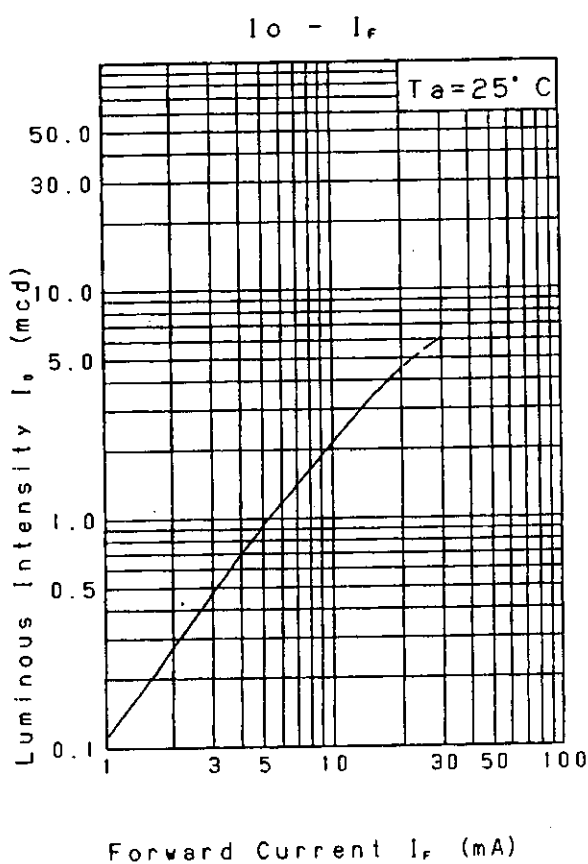
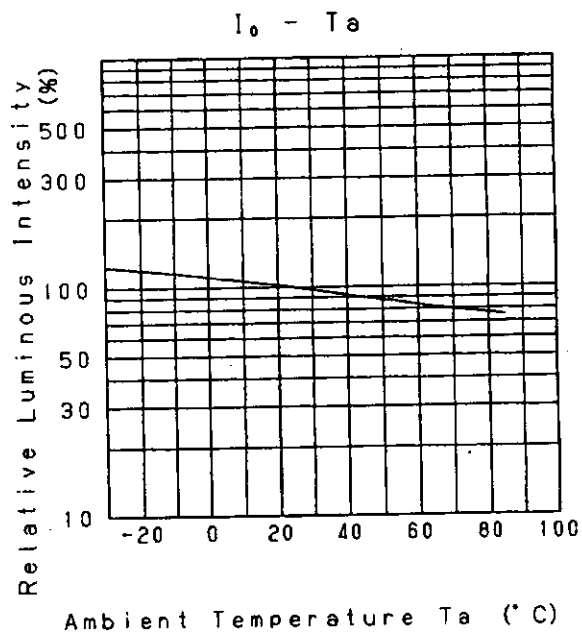
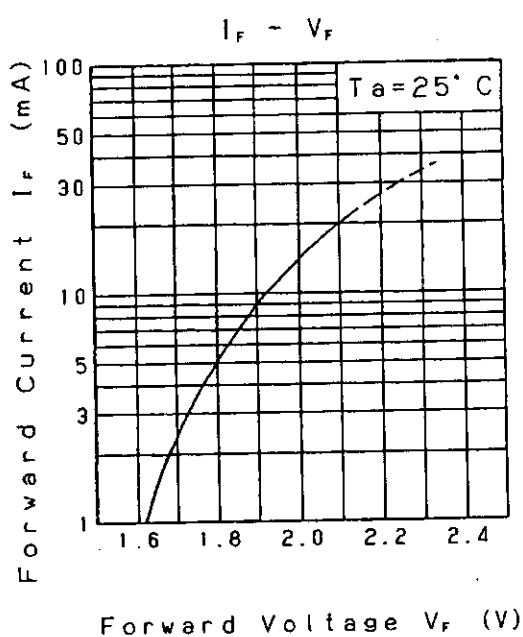


Approved	Checked	Designed	DEVELOPMENT SPECIFICATION							
	<i>h.h.</i>	<i>T. Takata</i>	P/N: LNJ816C8DRU							
T Y P E			Orange Light Emitting Diode							
APPLICATION			Indications							
MATERIAL			GaAsP							
OUTLINE			Attached							
ABSOLUTE			P	*1 I _{FP}	I _{FDC}	V _R	Topr	Tstg		
MAXIMUM			.60	100	20	3	-30~+85	-40~+100		
RATINGS			mW	mA	mA	V	°C	°C		
CONDITION			Ta = 25 ± 3°C							
Test Specification										
I t e m		Symbol	C o n d i t i o n			Typ	Limit		Unit	
							Min	Max		
Forward Voltage		V _F	I _F = 10 mA			1.93		2.6	V	
Reverse Leakage Current		I _R	V _R = 3 V					10	μA	
Luminous Intensity *2		I _O	I _F = 10 mA DC			2.1	1.1		mcd	
Peak Emission Wavelength		λ _p	I _F = 10 mA DC			630			nm	
Spectral Line Half Width		Δλ	I _F = 10 mA DC			40			nm	
*1 The Condition of I_{FP} is duty 10 %, Pulse width 1 ms *2 Tolerance of luminous intensity: ±20%. NOTE ★1. Please contact the Panasonic local office if you design at low current (below 1mA DC) or pulse current operation and have any questions. ★2. Soldering conditions.....Refer to Handling note. ★3. Care should be taken that soldering is done within 3-days after opening the dry package and reel. ★4. Compositions of the lead Cu/Ni/Au plating										
May. 28. 2001										

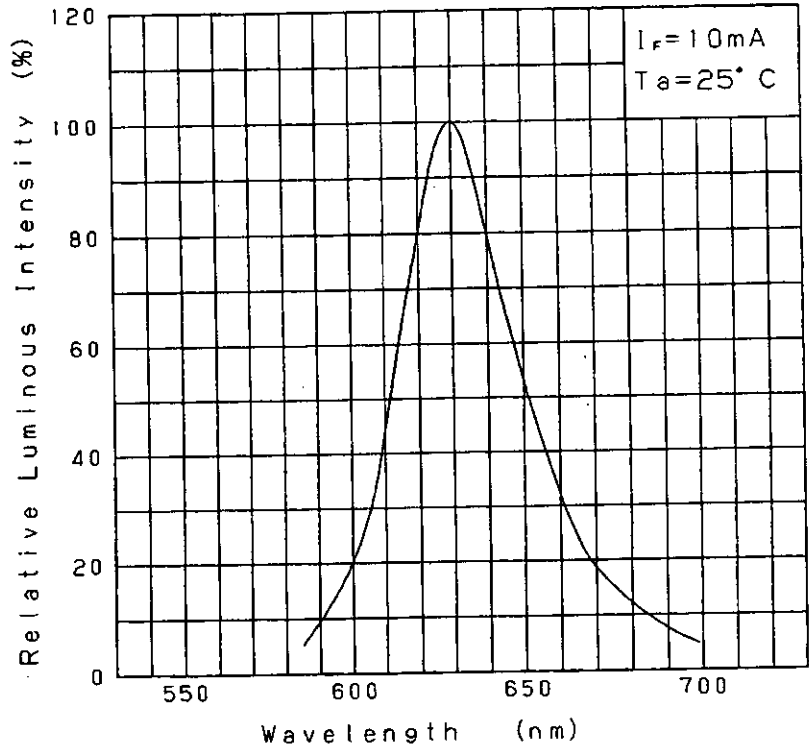
Approved	Checked	Designed	DEVELOPMENT SPECIFICATION		
	<i>h.h.</i>	<i>T. Tabata</i>	P/N: <u>LNJ816C8DRU</u>		



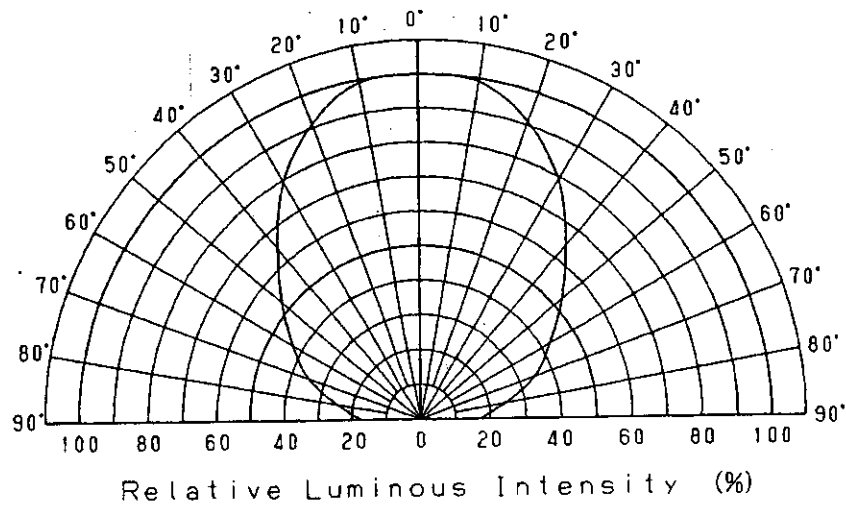
May. 28. 2001			

Approved	Checked	Designed	DEVELOPMENT SPECIFICATION		
	<i>M. W.</i>	<i>T. Takata</i>	P/N: LNJ816C8DRU		

Relative Luminous Intensity
Wavelength Characteristics

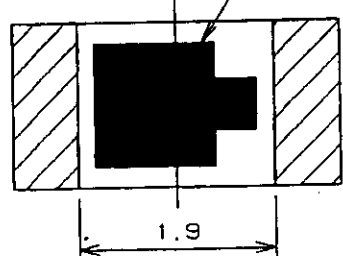
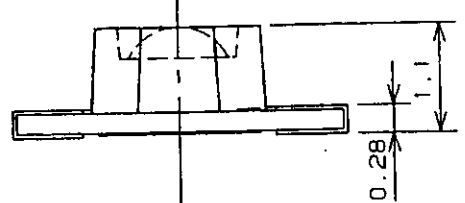
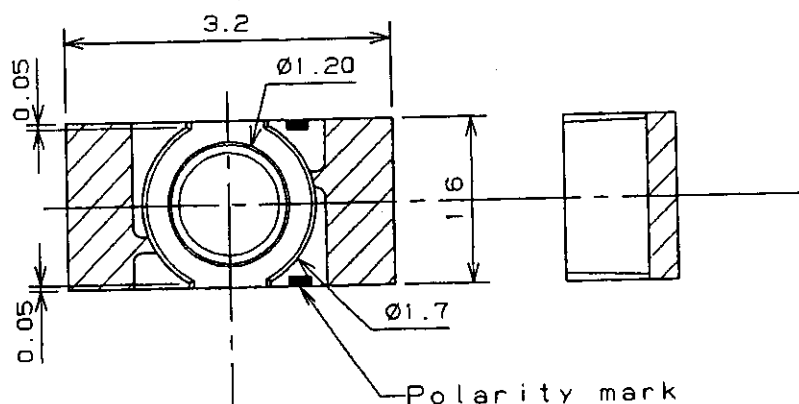


Directive Characteristics

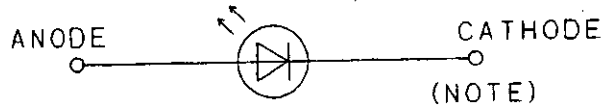
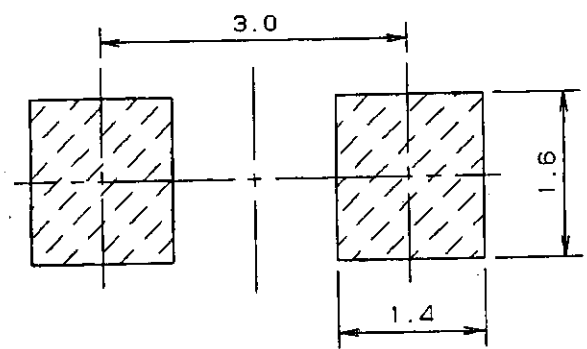


May.28.2001			

Approved	Checked	Designed	DEVELOPMENT SPECIFICATION (OUTLINE) P/N: LNJ816C8DRU		
	<i>M. W.</i>	<i>T. Takata</i>			



Recommended Land Layout



(NOTE)
1. Unit: mm
2. Tolerance unless specified is ± 0.15 .
3. indicate Au terminal.

Mar. 26. 2001			